35K202

Silicon N Channel 4-pole MOS Type

For VHF band high-gain low-noise amplification

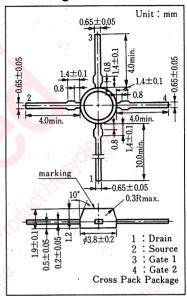
■ Features

- •Low noise figure NF
- •Large power gain PG
- •Cross pack package

■ Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Value	Unit
Drain-Source Voltage	V _{DSX}	15	V
Gate 1-Source Voltage	V _{G1S}	±8	V
Gate 2-Source Voltage	V_{G2S}	±8	V
Drain Current	I _D	30	m A
Power Dissipation	P _D	250	mW
Channel Temperature	Tch	135	° ° ° ° ° ° ° ° ° ° ° ° ° ° ° ° ° ° °
Storage Temperature	$T_{\rm stg}$	$-55 \sim +135$	r C

■ Package Dimensions



■ Electrical Characteristics (Ta=25°C)

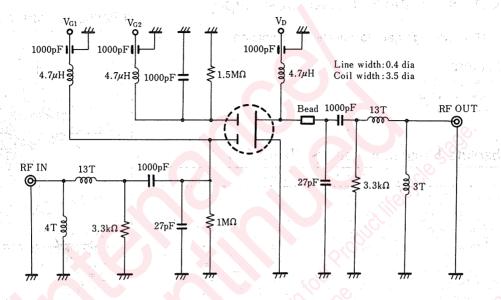
Item	Symbol	Condition	min.	typ.	max.	Unit
Drain-Source Voltage	V _{DSX}	$I_D = 50 \mu A$, $V_{GS} = -5 V$, $V_{G2S} = 0$ $R_D = 56 \Omega$, $R_S = 270 \Omega$	15		11/10/18	V
Gate 1-Source Cut off Current	V_{G1SC}	$V_{DS} = 10V$, $V_{G2S} = 4V$, $I_D = 100 \mu A$		-0.6	-3.0	V
Gate 2-Source Cutoff Current	V _{G2SC}	$V_{DS} = 10V$, $V_{G1S} = 4V$, $I_{D} = 100 \mu A$		-0.4	-3.0	V
Gate 1 Cutoff Current	I _{G1SS}	$V_{DS} = V_{G2S} = 0$, $V_{G1S} = \pm 8 \text{ V}$	70	(S)	±20	nA
Gate 2 Cutoff Current	I _{G2SS}	$V_{GS} = V_{G1S} = 0$, $V_{G2S} = \pm 8 V$	/	V.	±20	nA
Drain Current	I _{DSS} *1	$V_{DS} = 10V$, $V_{G1S} = 0$, $V_{G2S} = 4 V$	0.8		, 10	mΑ
Forward Transfer Admittance (Common Source)	Y _{fs}	$V_{DS} = 10V$, $V_{G2S} = 4 V$, $I_D = 10 \text{mA}$, $f = 1 \text{ kHz}$	25	30	,	mS
Input Capacitance	Ciss	$V_{DS} = 10V$, $V_{G1S} = V_{G2S} = -5V$, $f = 1 \text{ MHz}$	3.5	5.0	7.0	pF
Output Capacitance	Coss	$V_{DS}=10V$, $V_{G1S}=V_{G2S}=-5V$, $f=1 \text{ MHz}$	1.0	1.4	2.2	pF
Small-Signal Reverse Transfer Capacitance	Crss	$V_{DS} = 10V$, $V_{G1S} = V_{G2S} = -5 V$, $f = 1 MHz$		0.02		pF
Power Gain	PG ₁ *1,2	$V_{DS} = 8 \text{ V}, I_{D} = 8 \text{ mA},$ $V_{G2S} = 3 \text{ V}, f = 195 \sim 205 \text{MHz}$	20	25	30	đВ
Noise Figure	NF ₁ *1.2	$V_{DS} = 8 \text{ V}, I_D = 8 \text{ mA},$ $V_{G2S} = 3 \text{ V}, f = 195 \sim 205 \text{MHz}$		2.0	3.0	dB
Power Gain	PG ₂ *1,2	$V_{DS} = 8 \text{ V}, I_D = 8 \text{ mA}, V_{G2S} = 3 \text{ V}, f = 45 \sim 55 \text{MHz}$	22	26	32	dB
Noise Figure	NF ₁ .*1,2	$V_{DS} = 8 \text{ V}, I_D = 8 \text{ mA}, V_{G2S} = 3 \text{ V}, f = 45 \sim 55 \text{MHz}$		3.8	4.5	dB

*IDSS Ranking

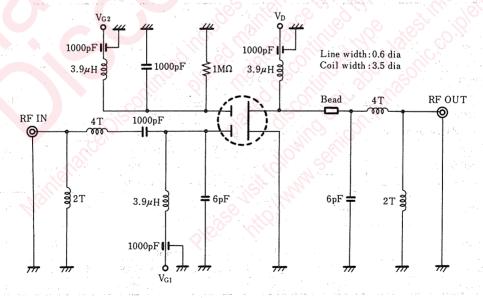
Rank	· Q	R
I _{DSS} (mA)	0.8~7.0	4.0~10

Note: In the range of f:PG=max. value and NF=min. value

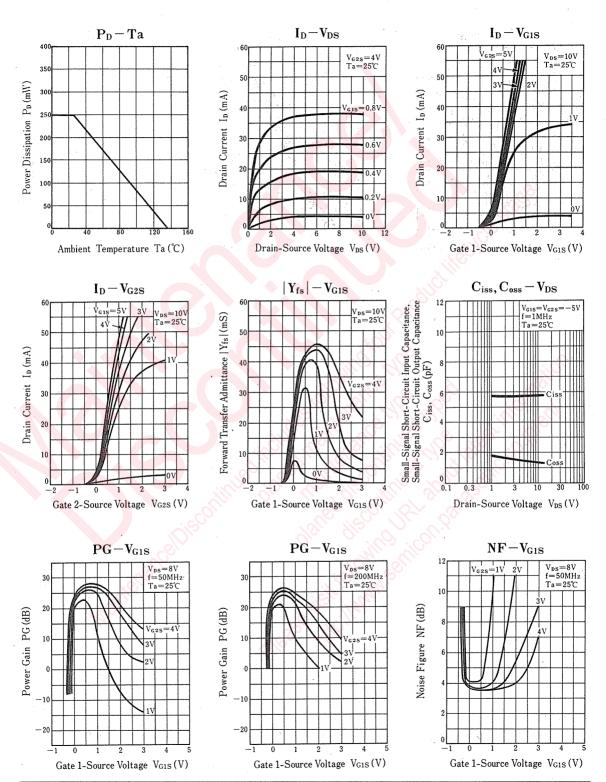
*2 PG, NF Measuring Circuit (f=50MHz)

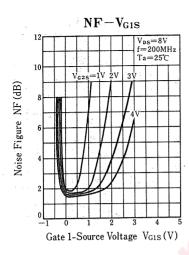


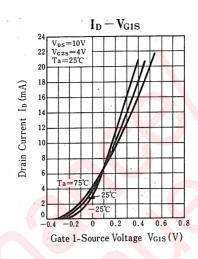
*3 PG, NF Measuring Circuit (f=200MHz)











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